NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TPV3100** is a Class AB Common Device Designed for Television Band IV & V Applications.

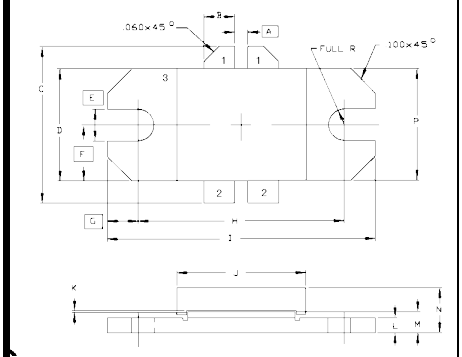
FEATURES INCLUDE:

- Gold Metalization
- Emitter Ballasting
- Internal Matching

MAXIMUM RATINGS

I_C	12 A
V_{CC}	65 V
P_{DISS}	215 W @ T_C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	0.80 °C/W

PACKAGE STYLE .450 BAL FLG.(A)



	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
	.055/1.40		K	.002/0.05	.006/0.15
B	.120/3.05	.130/3.30	L	.055/1.40	.065/1.65
C		.785/19.94	M	.080/2.03	.095/2.41
D	.455/11.56	.465/11.81	N		.195/4.95
E	.130/3.30		P	.455/11.56	.468/11.89
F	.230/5.84				
G	.120/3.05				
H	.838/21.28	.850/21.59			
I	1.095/27.81	1.105/28.07			
J	.525/13.34	.535/13.59			

1 = Collector 2 = Base
3 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 20 mA			65			V
BV_{CER}	I_C = 10 mA	R_{BE} = 75 Ω		30			V
BV_{EBO}	I_E = 10 mA			4.0			V
I_{CER}	V_{CE} = 28 V	R_{BE} = 75 Ω				10	mA
h_{FE}	V_{CE} = 10 V	I_C = 2.0 A		30		120	—
P_{1dB}	V_{CE} = 28 V	I_{CQ} =2X50 mA	Fo = 860 MHz	100			W
P_g	V_{CE} = 28 V	I_{CQ} =2X50 mA	Fo = 860 MHz	8.5	9.5		dB